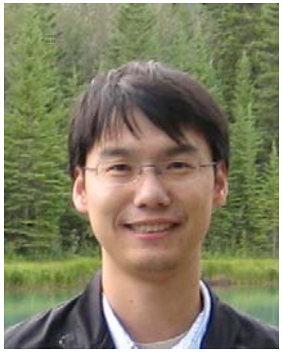
Controlling the valley degree of freedom in Graphene systems

Qian Niu

University of Texas at Austin



Dr. Di Xiao

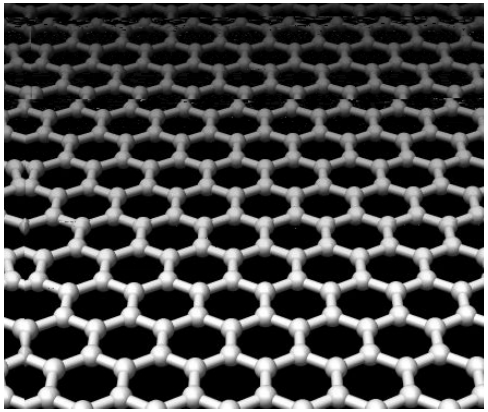
Dr. Tianyi Cai

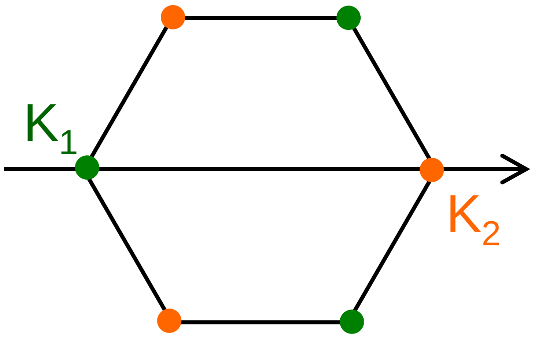
Dr. Wang Yao

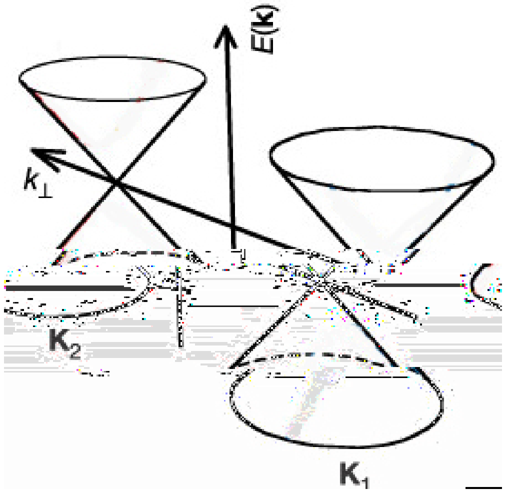
Outline

- The valley index in graphene and inversion symmetry breaking
- Valley contrasting magnetic moment and Berry curvature
- Magnetic control: valley polarization and magnetism
- Electrical control: valley Hall effect and inverse
- Optical control: valley dependent circular dichroism

Valley degree of freedom in Graphene







- **Valley index in graphene**

  Two inequivalent valleys related by time reversal symmetry

- **Long intervalley scattering time**
  - ~ 100 ps observed in bilayers. Gorbachev et al., PRL 07"
  - Valleytronics: analogy to spintronics. Beenakker et al. 07"
- **How to control the valley degree of freedom?**

Learning from spintronics

- Spin has a magnetic moment: magnetic control
- Spin-orbit coupling: electrical control (spin Hall effect)
- Spin-dependent cicular dichroism: optical control

- How to control the valley degree of freedom?

Three basic electronic properties

1. Band energy: particle or hole, effective mass,..
2. Magnetic moment: spin and orbital moment
3. Berry curvature: Berry phase effects

$$\varepsilon_n(\boldsymbol{k}) = \varepsilon_n^0(\boldsymbol{k}) - \boldsymbol{m}(\boldsymbol{k}) \cdot \boldsymbol{B}$$

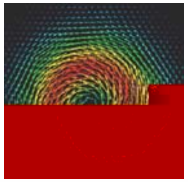
$$\dot{\boldsymbol{r}} = \frac{1}{\hbar}\frac{\partial \varepsilon_n(\boldsymbol{k})}{\partial \boldsymbol{k}} - \dot{\boldsymbol{k}} \times \boldsymbol{\Omega}_n(\boldsymbol{k})$$

$$\hbar\dot{\boldsymbol{k}} = -e\boldsymbol{E} - e\dot{\boldsymbol{r}} \times \boldsymbol{B}$$

Berry curvature

$$\boldsymbol{\Omega}_n(\boldsymbol{k}) = i\left\langle \frac{\partial u_{n\boldsymbol{k}}}{\partial \boldsymbol{k}} \right| \times \left| \frac{\partial u_{n\boldsymbol{k}}}{\partial \boldsymbol{k}} \right\rangle$$

Magnetic moment



$$\boldsymbol{m}(\boldsymbol{k}) = -\frac{e}{2}\langle W|(\hat{\boldsymbol{r}} - \boldsymbol{r}_c) \times \boldsymbol{v}|W\rangle$$
$$= -i\frac{e}{\hbar}\left\langle \frac{\partial u}{\partial \boldsymbol{k}} \right| \times (\hat{H} - \varepsilon_{\boldsymbol{k}}^0) \left| \frac{\partial u}{\partial \boldsymbol{k}} \right\rangle$$

Our goal: engineer valley-dependent magnetic moment and Berry curvature.

Symmetry Consideration

Time-reversal symmetry $\Omega(\boldsymbol{k}) = -\Omega(-\boldsymbol{k})$ $m(\boldsymbol{k}) = -m(-\boldsymbol{k})$

Space-inversion symmetry $\Omega(\boldsymbol{k}) = \Omega(-\boldsymbol{k})$ $m(\boldsymbol{k}) = m(-\boldsymbol{k})$

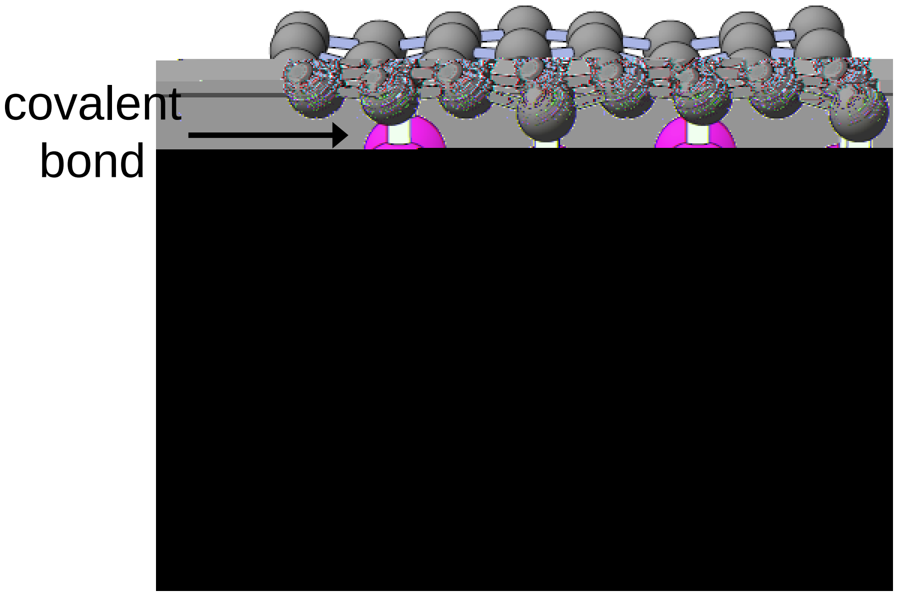
Both symmetries $\Omega(\boldsymbol{k}) = 0$ $m(\boldsymbol{k}) = 0$

Need to break time-reversal (ferromagnet)
or spatial inversion symmetries.

Inversion Asymmetry in Eptixially Graphene

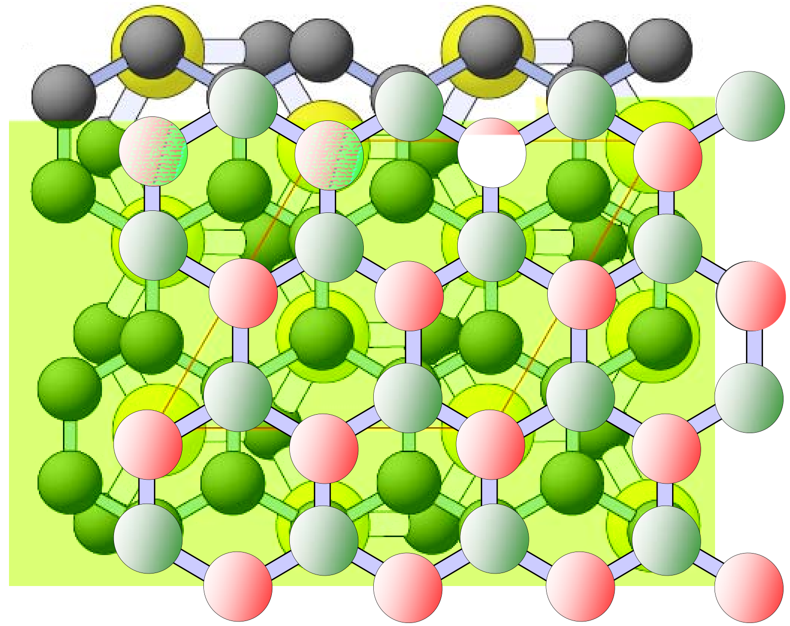
Side view

1st carbon layer: **‘dead’** layer



Top view

2nd carbon layer: **active** layer



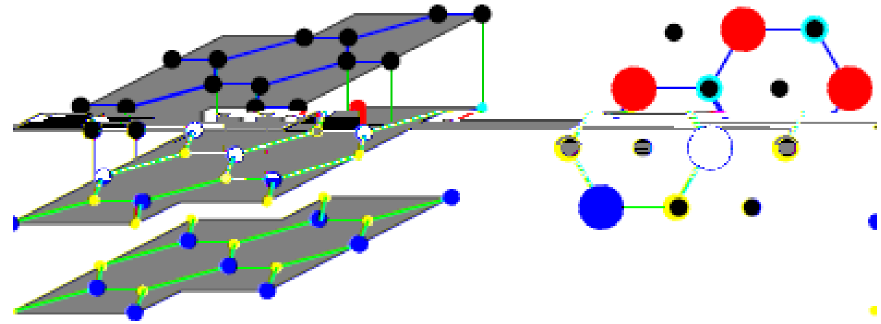
Site energy difference between A and B ⇨ broken inversion symmetry

Mattausch & Pankratov [arXiv:0704.0216]

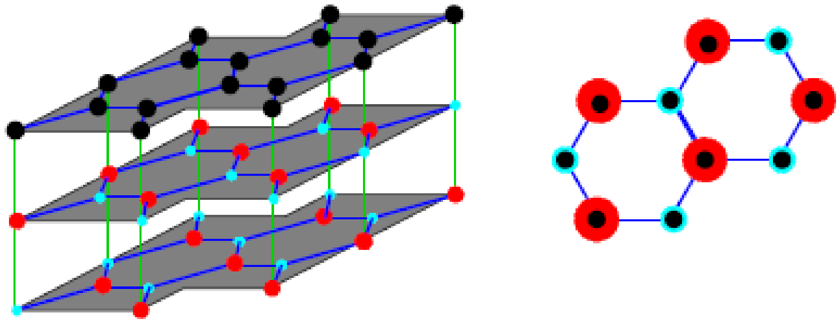
Graphene on Boron Nitride

Giovannetti *et al.* arXiv:0704.1994

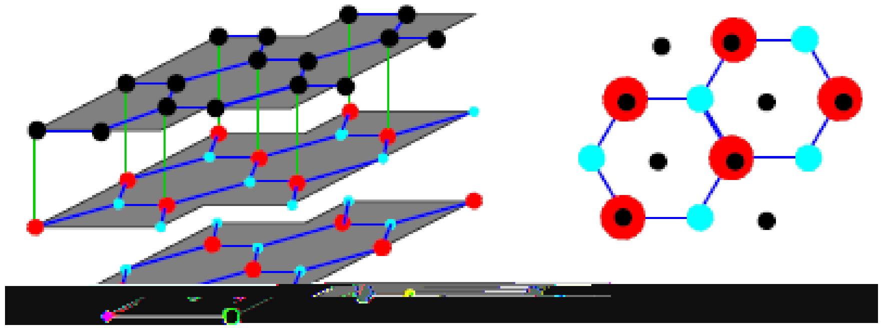
one sublattice on Boron



A on Boron / B on Nitride



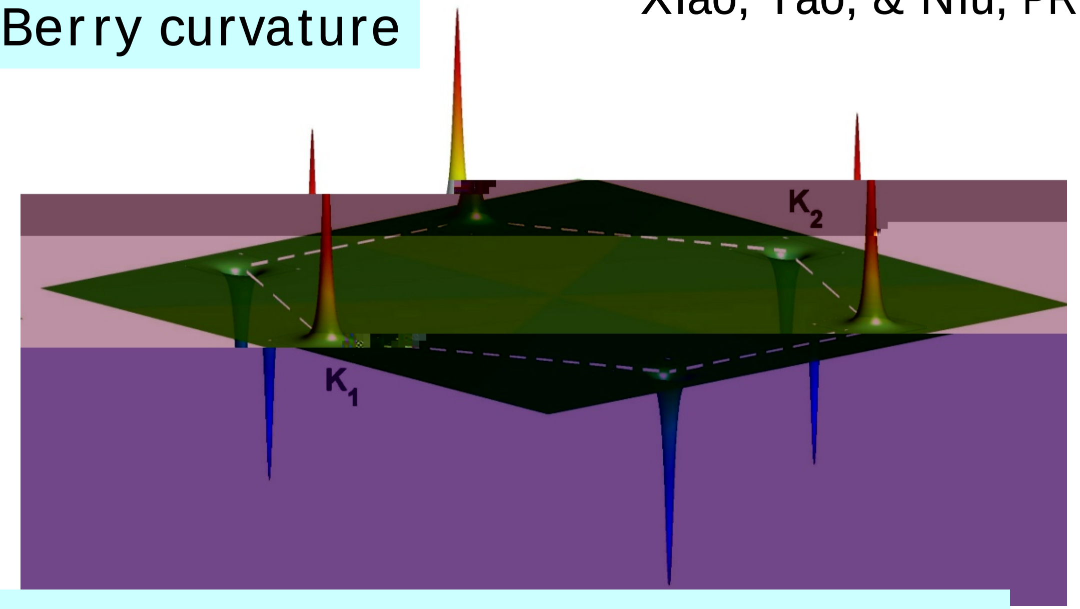
one sublattice on Nitride



Valley Contrasting Berry Curvature

Berry curvature

Xiao, Yao, & Niu, PRL 07"

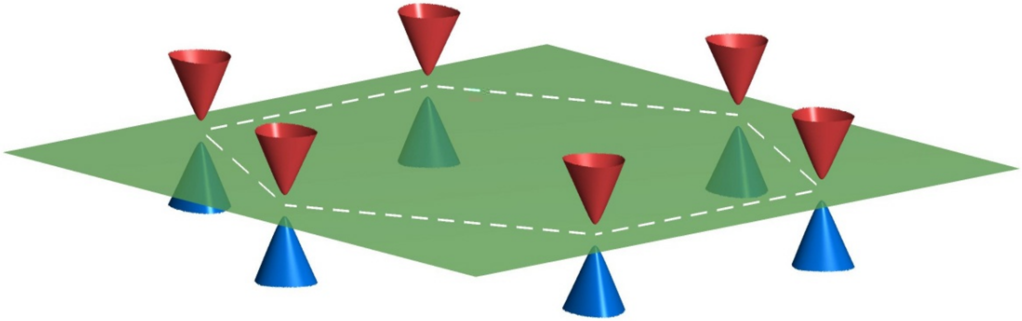


$$\Omega(\boldsymbol{q}) = \tau_z \frac{3\Delta t^2}{2(\Delta^2 + 3q^2a^2t^2)^{3/2}}$$

Valley index

$\tau_z = 1\ (-1)$ for valley K_1 (K_2)

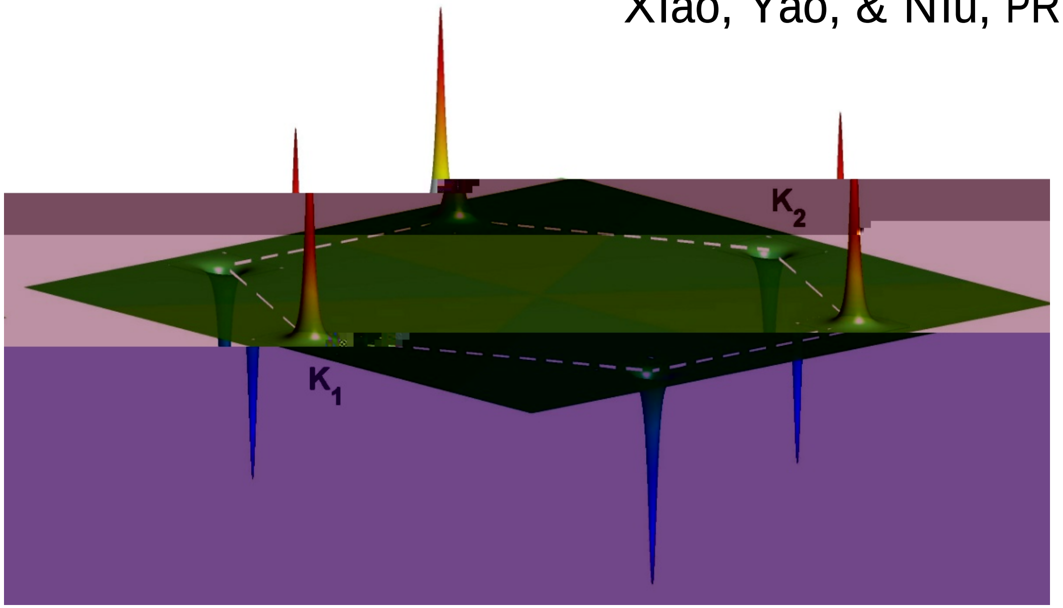
Energy dispersion: massive Dirac bands



$$\varepsilon(q) = \pm\sqrt{\Delta^2 + 3t^2q^2a^2/4}$$

Valley Magnetic Moment

Xiao, Yao, & Niu, PRL 07”



$$m(\boldsymbol{k}) = \tau_z \frac{3ea^2\Delta t^2}{4\hbar(\Delta^2 + 3q^2a^2t^2)}$$

Valley index

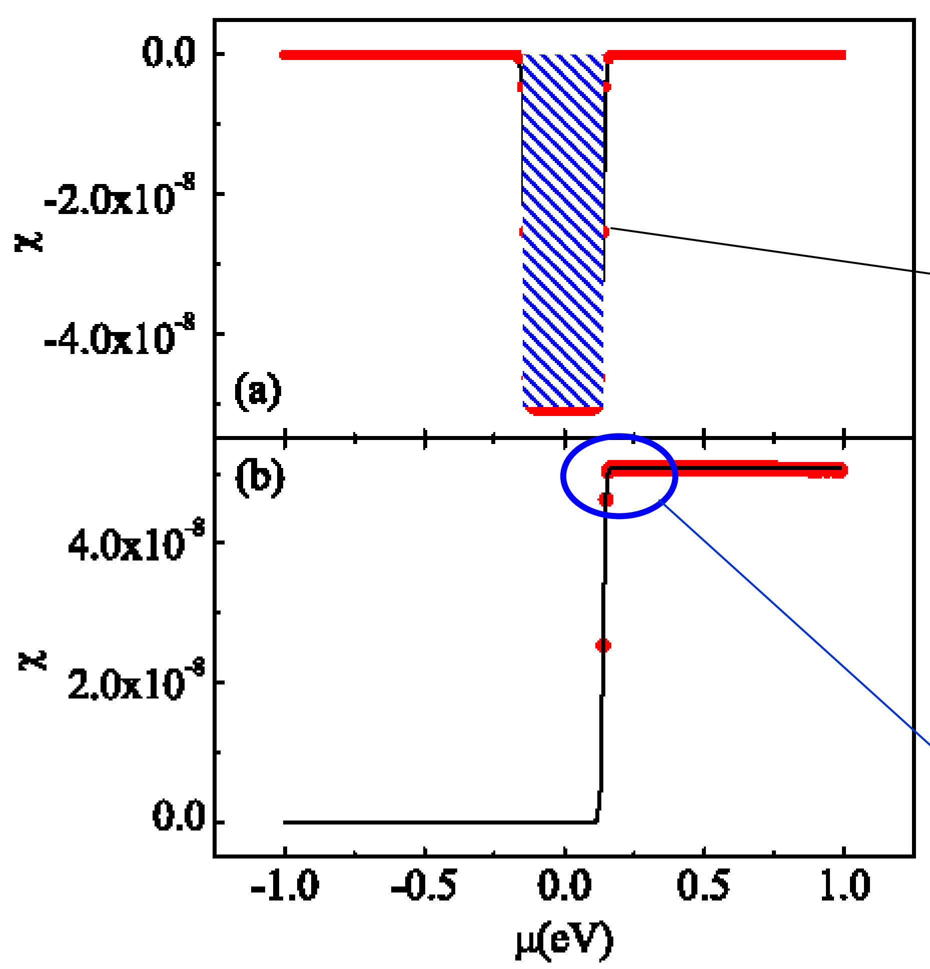
$\tau_z = 1\ (-1)$ for valley K_1 (K_2)

– At band bottom: $m(\boldsymbol{K}_{1,2}) = \tau_z \mu_B^*$, $\mu_B^* = \frac{e\hbar}{2m_e^*}$

– Valley index is associated with an intrinsic magnetic moment

$$\mu_B^* \sim 30\mu_B$$

Magnetic Susceptibility



- All bands

$$\chi = \frac{e^2a^2t}{4\pi Z^2\Delta}\frac{e^{\beta\mu}\left(e^{\beta\Delta/2}-e^{-\beta\Delta/2}\right)}{1+2e^{\beta\mu}Cosh\left(\beta\Delta/2\right)+e^{2\beta\mu}}$$

- Conduction bands only

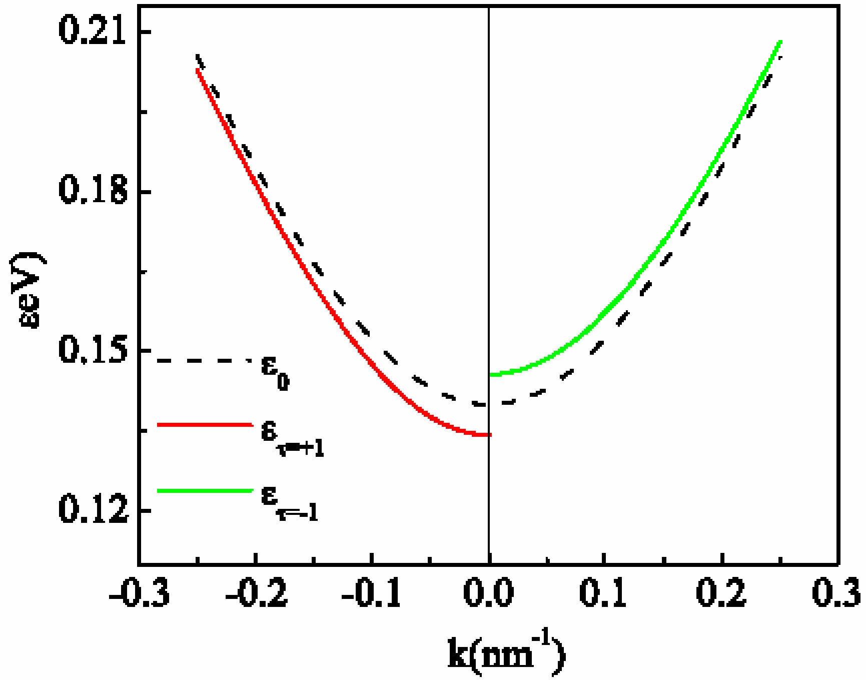
$$\chi_V = \frac{e^2a^2t}{4\pi Z^2\Delta}\frac{1}{1+e^{-\beta(\mu-\Delta/2)}}$$

$$\chi_V = \chi_p + \chi_d = \frac{e^2}{6\pi m^*} \qquad \begin{cases} \chi_p = \dfrac{3e^2a^2t^2}{8\pi Z^2\Delta} \\ \chi_d = -\dfrac{e^2a^2t^2}{8\pi Z^2\Delta} \end{cases}$$

Magnetic control of valley polarization

K1 valley
τ=+1

K2 valley
τ=-1



$$E = E_0 - m \cdot B$$

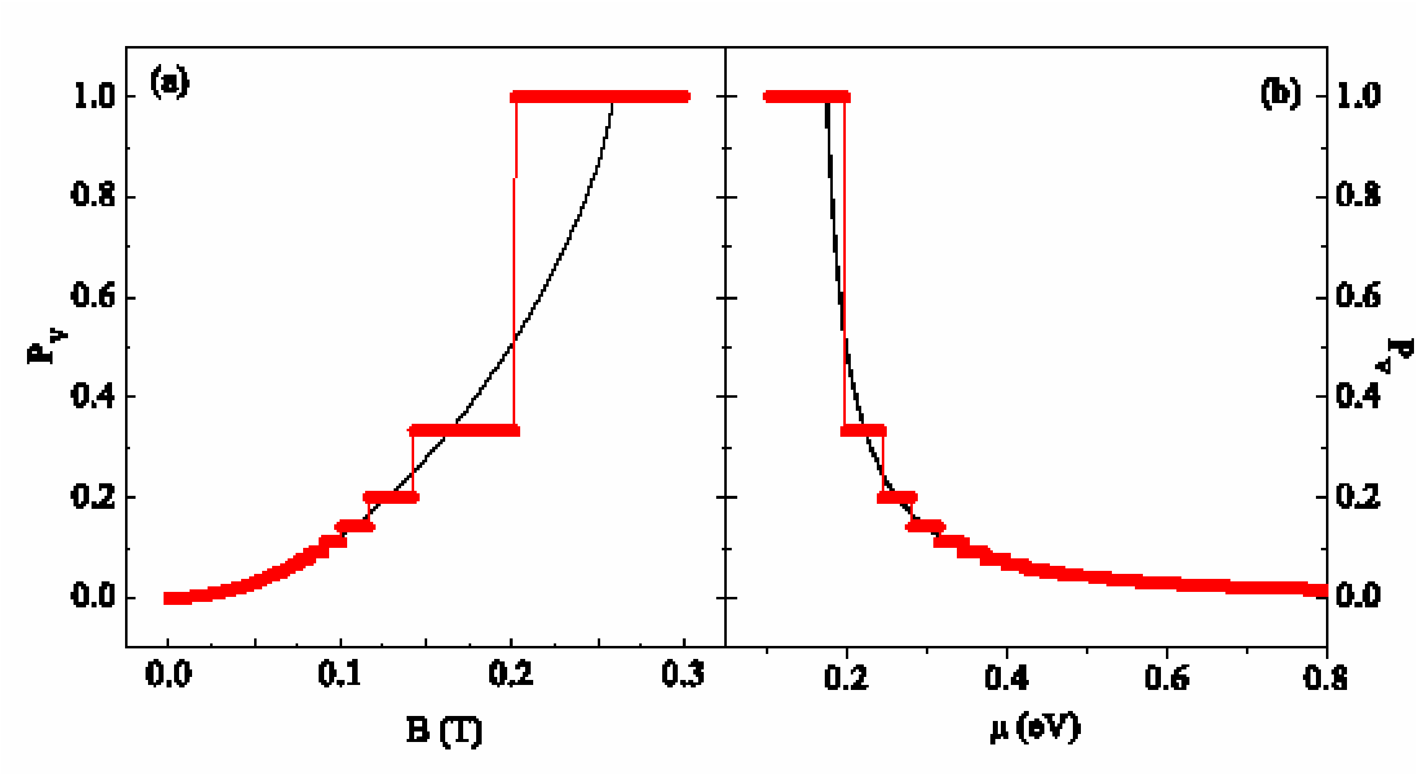
- Valley polarization

$$P_V = \frac{N_{+1} - N_{-1}}{N_{+1} + N_{-1}}$$

- Berry phase correction

$$N_\tau = \int_0^{k_F} \frac{1}{(2\pi)^2} \left(1 + \frac{eB \cdot \Omega_\tau}{Z}\right) dk$$

Magnetic control of valley polarization



The variations of valley polarization with magnetic field and chemical potential.

Magnetization from valley polarization

– Valley contrasting orbital magnetization

$$M = 2\int \frac{d\boldsymbol{k}}{(2\pi)^2}[m(\boldsymbol{k}) + (e/\hbar)(\mu - \varepsilon(\boldsymbol{k}))\Omega(\boldsymbol{k})]$$

$$= 2(e/\hbar)\mu \boxed{\int \frac{d\boldsymbol{k}}{(2\pi)^2}\Omega(\boldsymbol{k})} \rightarrow \frac{C(\mu)}{2\pi}$$

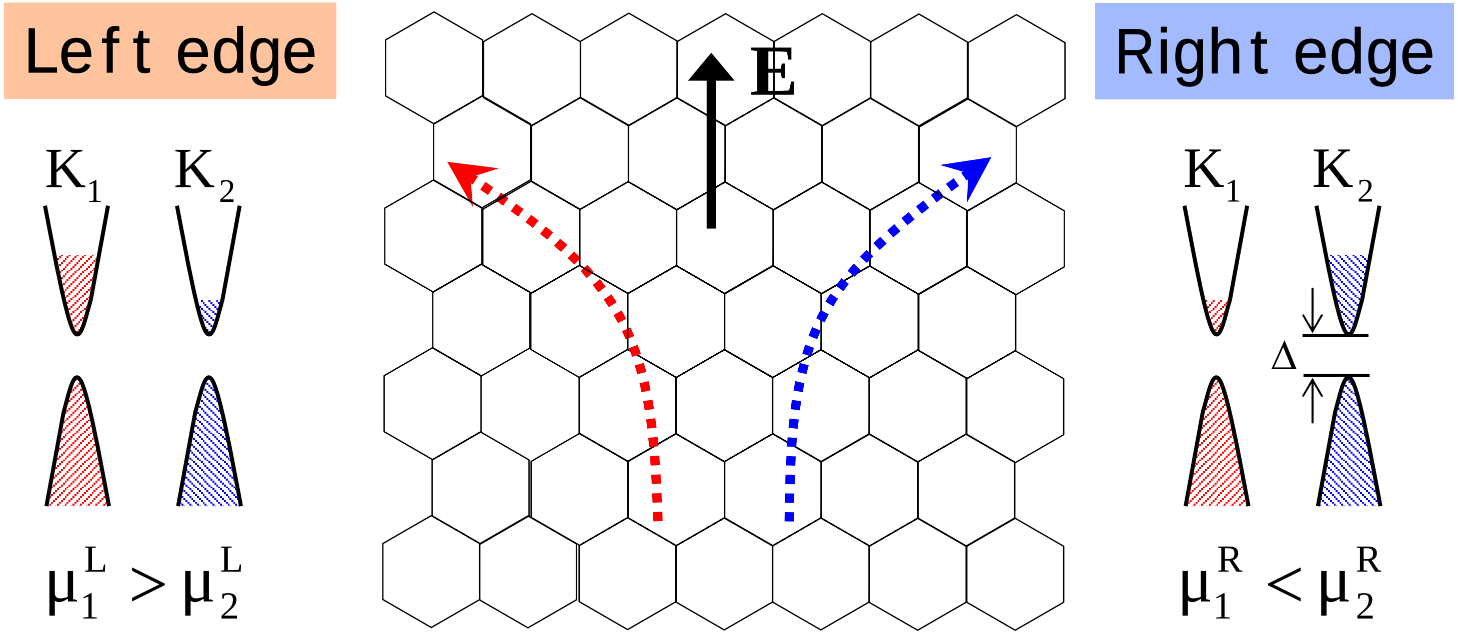
$$C(\mu) \rightarrow \frac{\tau_z}{2} \quad \text{for } \mu >> \Delta$$

Berry phase of π

– Net orbital magnetization by valley polarization

$$\delta M = 2\frac{e}{\hbar}[\mu_1 \frac{\mathcal{C}_1(\mu_1)}{2\pi} + \mu_2 \frac{\mathcal{C}_2(\mu_2)}{2\pi}] \approx 2\frac{e}{h}\mathcal{C}_1(\mu)\delta\mu$$

Valley Hall Effect - Electric Control

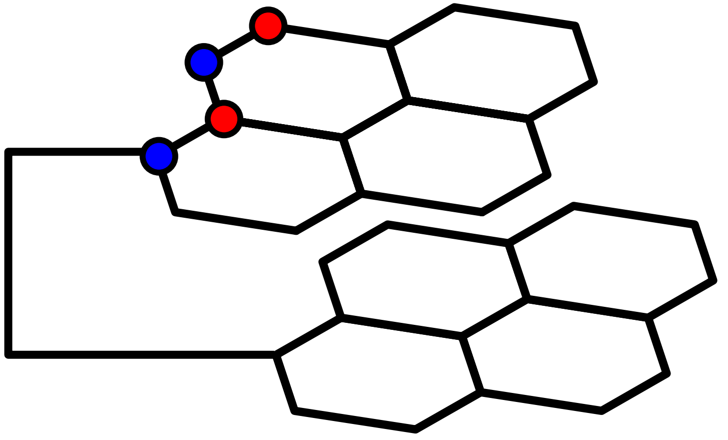


Valley polarization on edge: $$\int \delta n_v \, dx = j_x^v \tau_v = 2\frac{\sigma_H \tau_v}{e} E_y$$

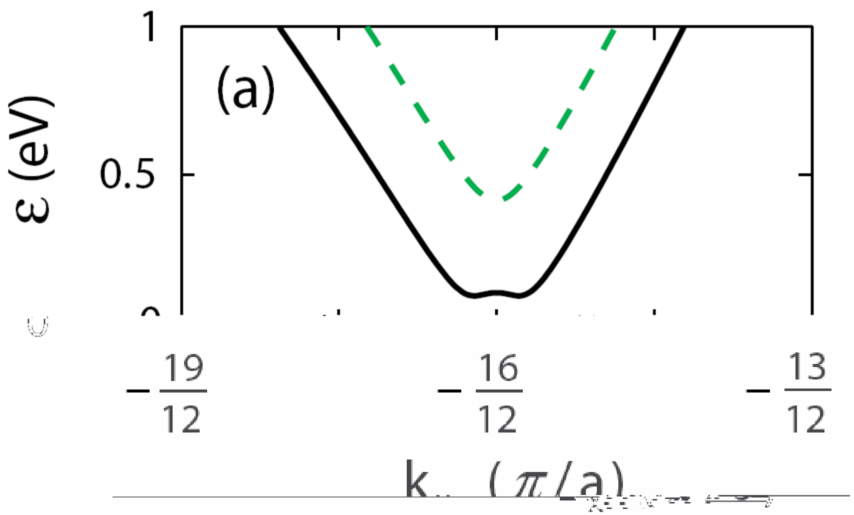
Edge magnetization: $$M_{\text{edge}} = \int \delta M \, dx = \frac{4}{h}\frac{\partial \mu}{\partial n}\mathcal{C}_1(\mu)\sigma_H \tau_v E$$

$\sim 100\,\mu_B/\mu\text{m}^2$ for $E \sim \text{mV}/\mu\text{m}$

Xiao, Yao, & Niu, PRL 07"

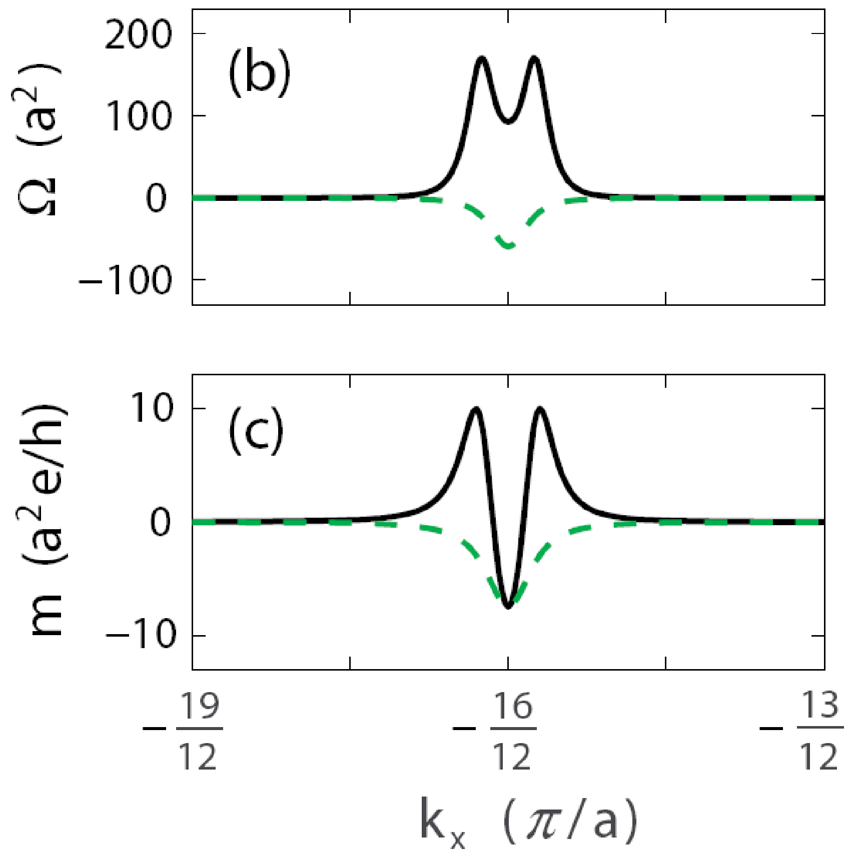


Berry Curvature and Orbital Moment in BGB



ARPES, Rotenberger group, 06”

valley K_1, conduction

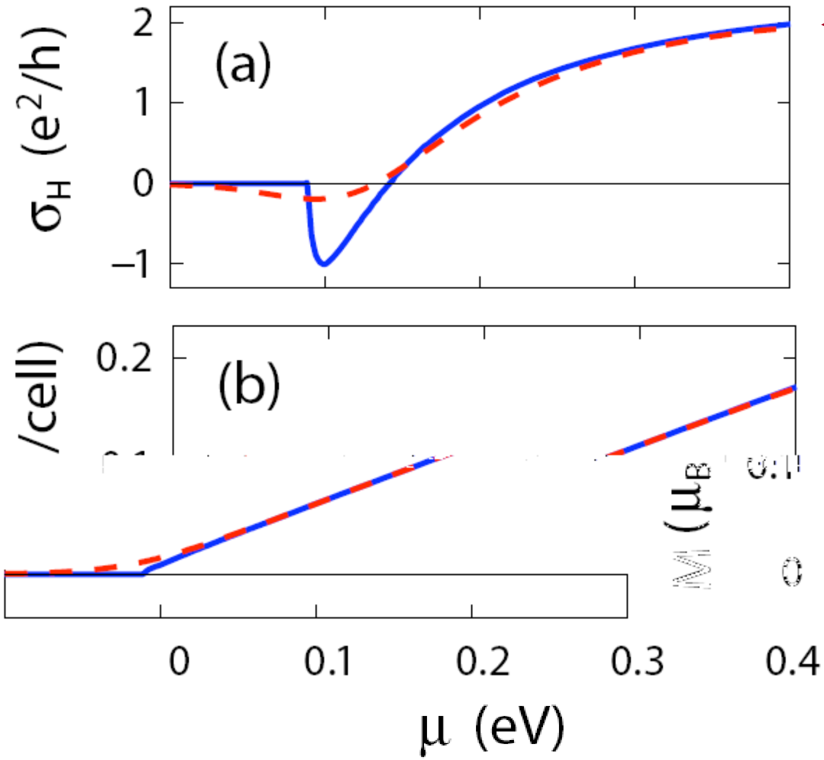


Xiao, Yao & Niu, PRL 07”

Opposite Ω(k) and m(k) at valley K_2

Valance band: opposite Ω(k) but same m(k)

Valley Hall Conductance in BGB



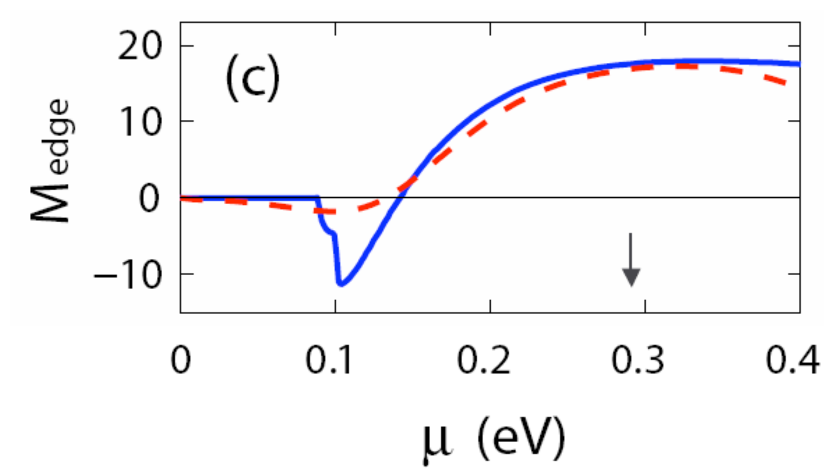
approaching quantized value

Berry phase of 2π in bilayer

(left up) Hall conductance &
(left down) orbital magnetization
in valley K_1

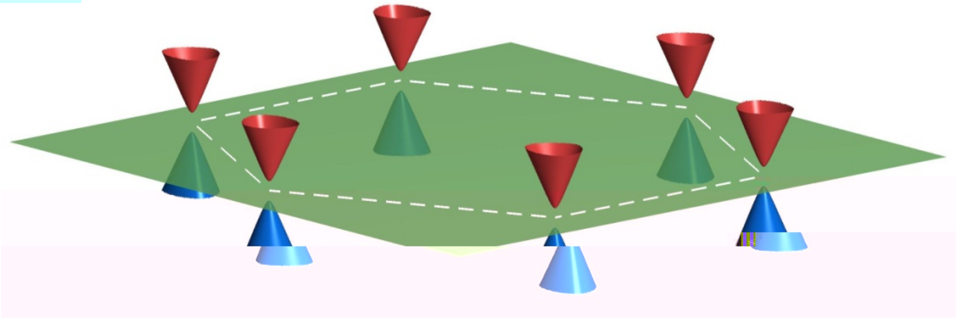
(right) edge magnetization in
Hall geometry

$$M_{edge} = 2\frac{\partial M}{\partial \mu}\frac{\partial \mu}{\partial n}\sigma_H^v \tau_v E_y$$



Optical Interband Transitions?

Energy dispersion



- Valley contrasted magnetic moment and Hall current
- Finite bandgap -> optical interband transitions
- In atoms: selection rule by magnetic moment
- Selection rule in III-V material: inheritance from parent orbitals
- Graphene: c-band and v-band originate from the same orbital

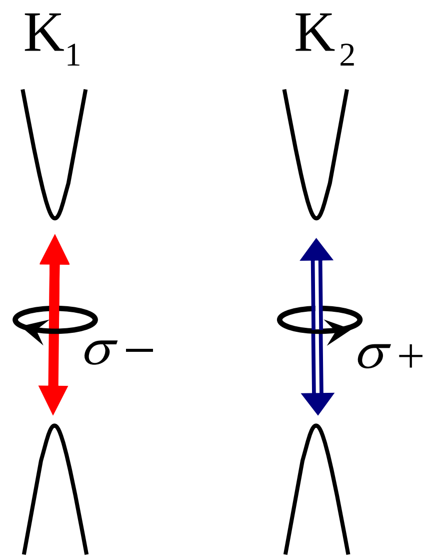
$$\mathcal{P}_{cv}^{\pm} \equiv \langle u_{c,\boldsymbol{k}}|\hat{p}_x \pm i\hat{p}_y|u_{v,\boldsymbol{k}}\rangle = \frac{m_0}{\hbar}\langle u_{c,\boldsymbol{k}}|\frac{\partial H}{\partial k_x} \pm i\frac{\partial H}{\partial k_y}|u_{v,\boldsymbol{k}}\rangle$$

Valley Contrasting Optical Selection Rules

– Matrix element of interband transition

$$|\mathcal{P}_{cv}^{\pm}(\boldsymbol{k})|^2 = m_0^2 v_0^2 (1 \mp \tau_z \cos\theta)^2$$

$\cos\theta$. 1 near Dirac points

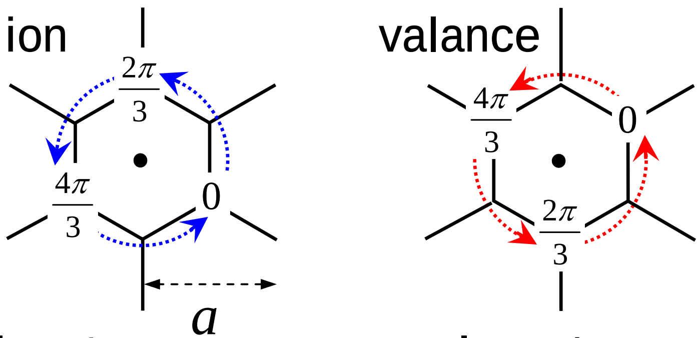


Valley optical selection rule

Phase winding of Bloch function at K_1

conduction

valance



$l_c = 1$ $l_v = -1$

Effective azimuthal rule

$l_v + j = l_c + 3N$

WY, Xiao & Niu, arXiv:0705.4683

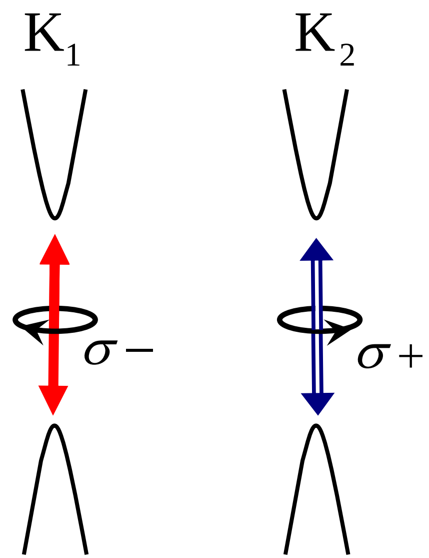
Valley Contrasting Optical Selection Rules

- Matrix element of interband transition

$$|\mathcal{P}_{cv}^{\pm}(\boldsymbol{k})|^2 = m_0^2 v_0^2 (1 \mp \tau_z \cos\theta)^2$$

$\cos\theta \;.\; 1$ near Dirac points

Valley optical selection rule



- Optical strength

$\left|P_{cv}\right|^2 / m_0 \sim 5\ \mathrm{eV}$ (~ 21.5 eV in GaAs)

- Far away from Dirac points

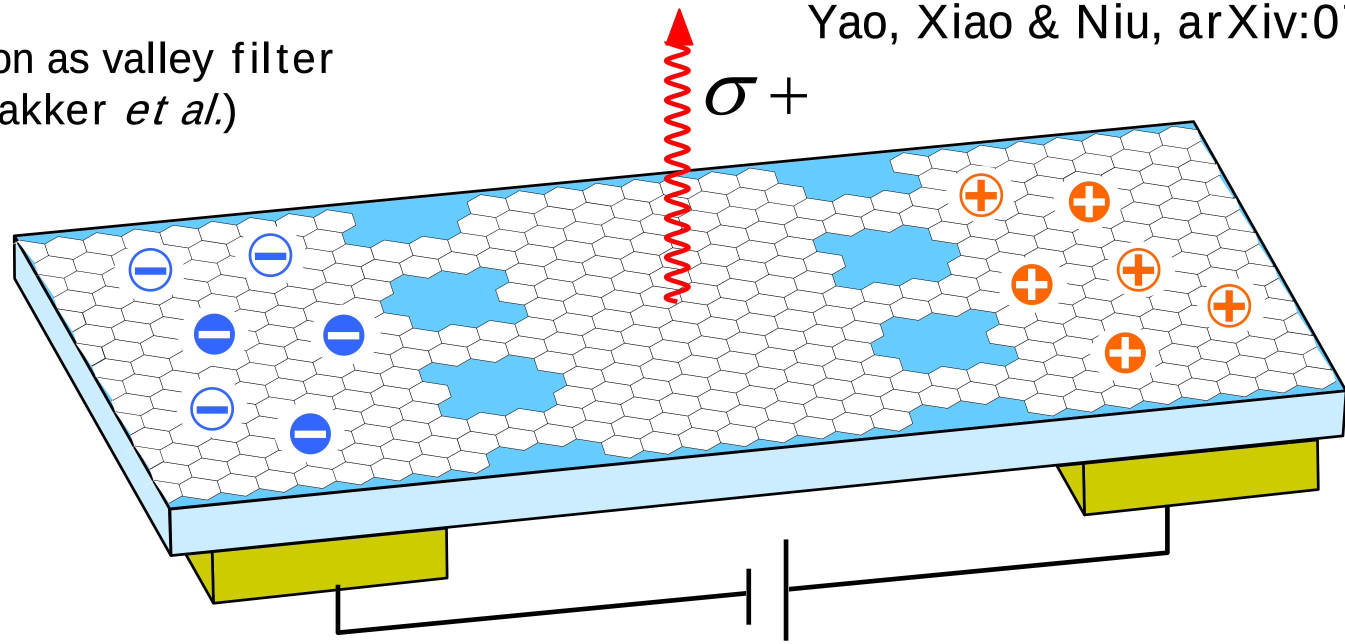
No circular dichroism, constant high frequency optical conductivity

WY, Xiao & Niu, arXiv:0705.4683

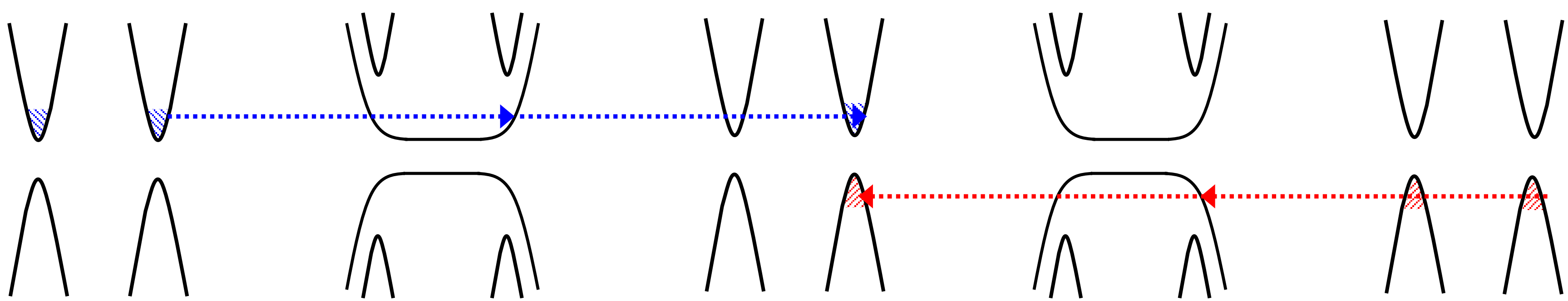
Valley LED

Yao, Xiao & Niu, arXiv:0705.4683

Nano-ribbon as valley filter
(Beenakker *et al.*)



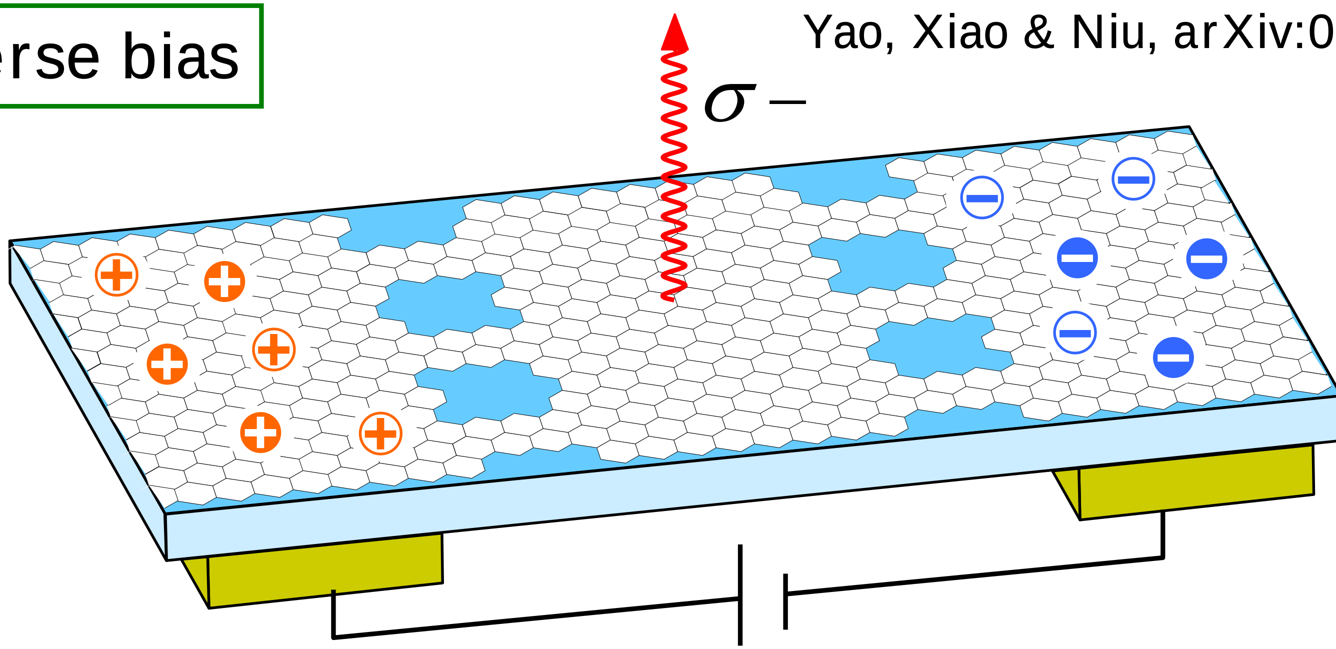
N - region | QPC | Intrinsic | QPC | P - region

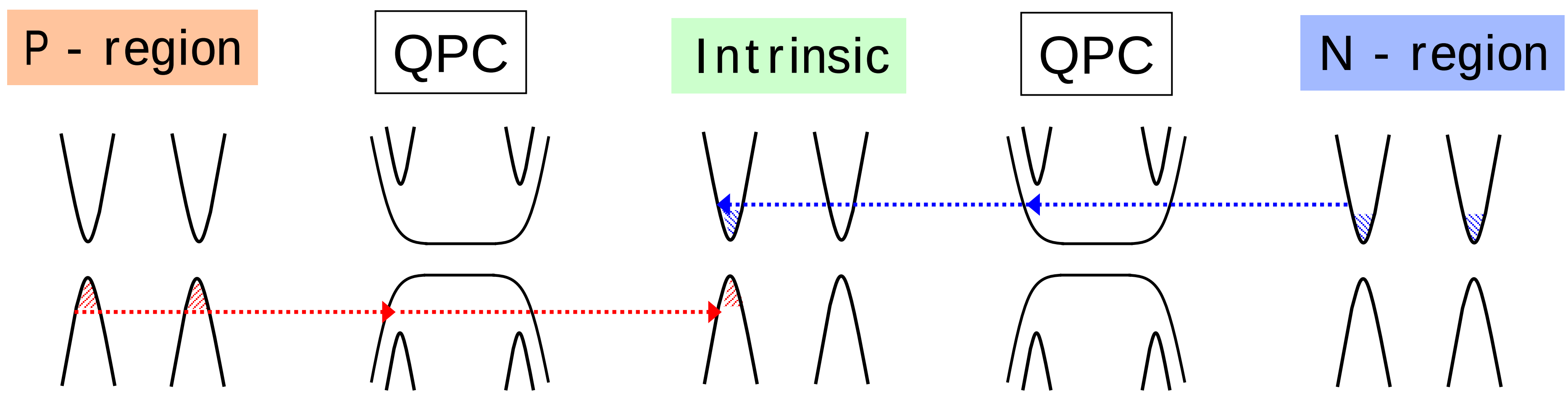


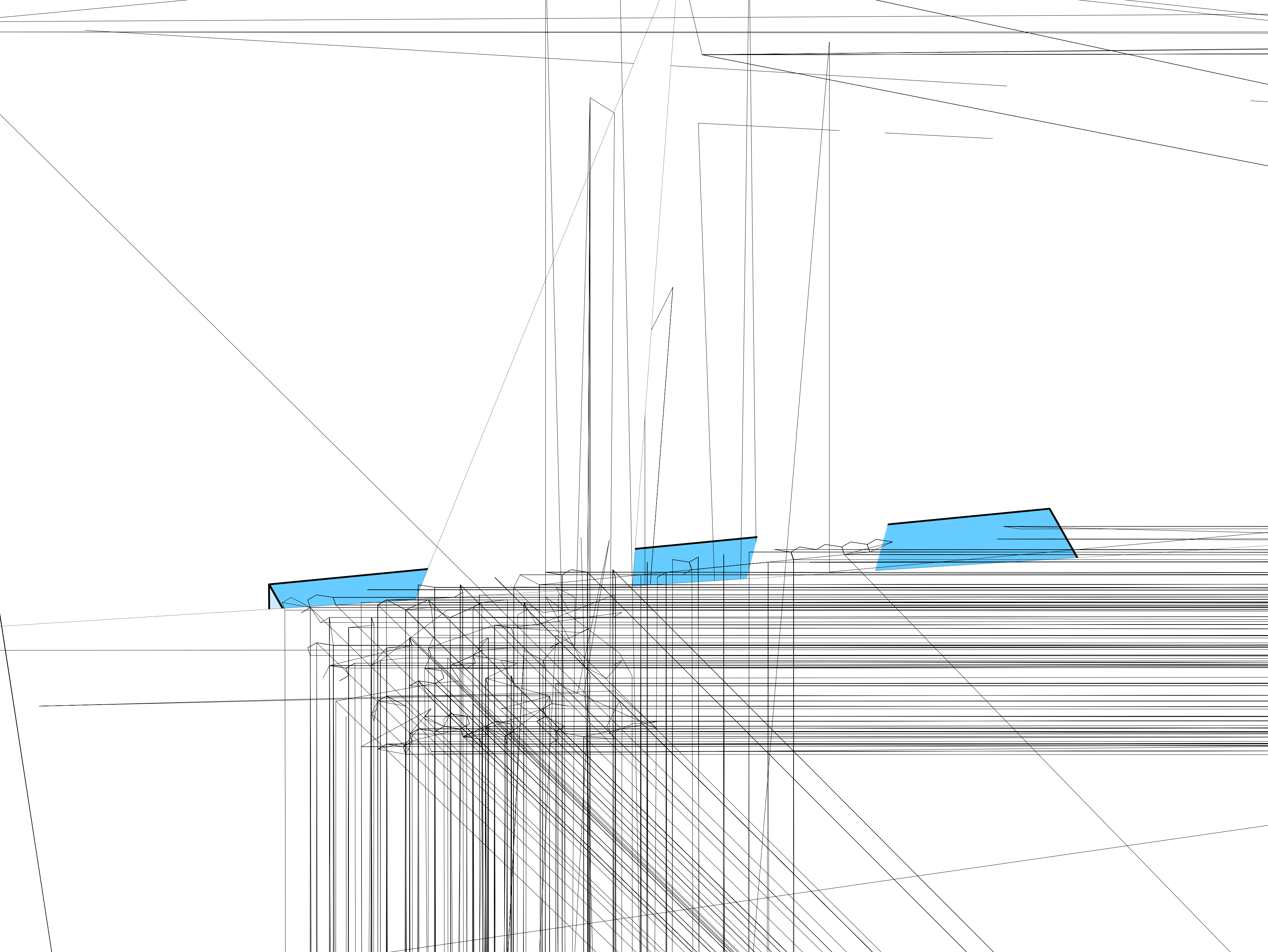
Valley LED

Reverse bias

Yao, Xiao & Niu, arXiv:0705.4683

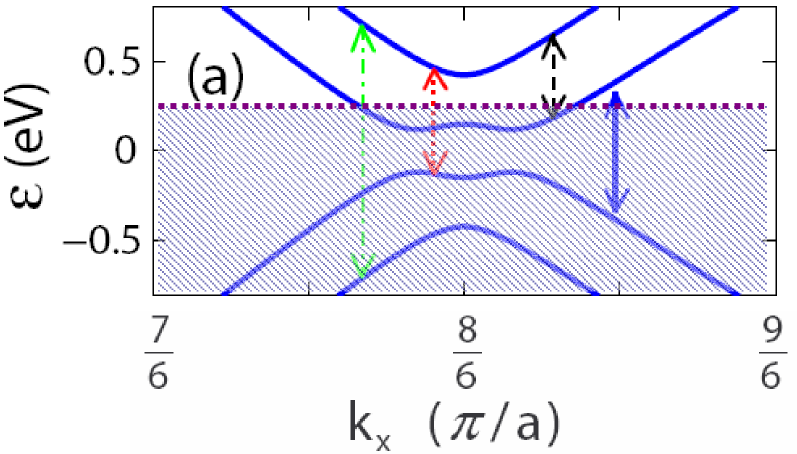


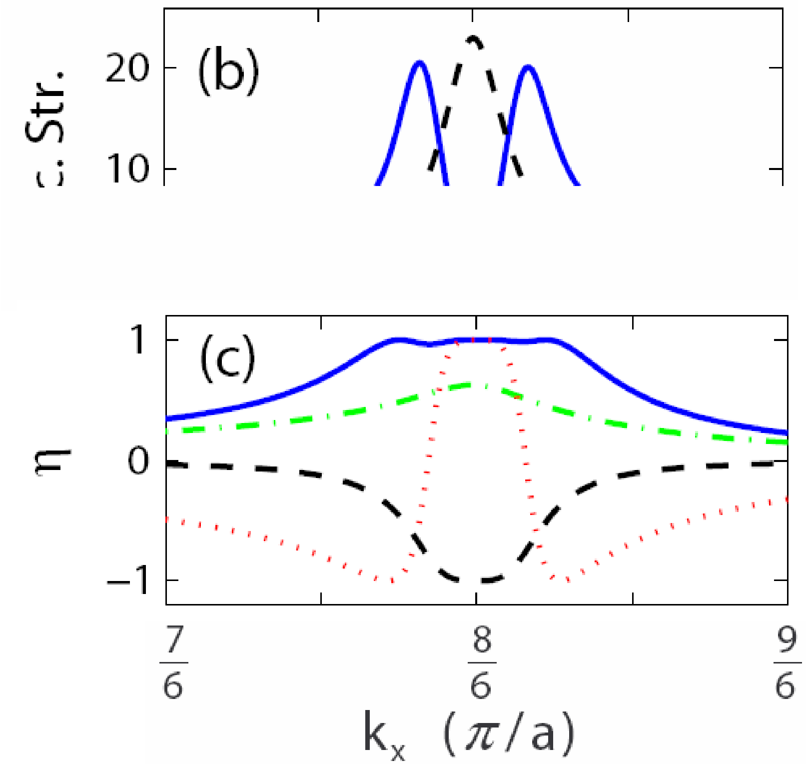




Bilayer with Interlayer Gate Voltage

WY, Xiao & Niu, arXiv:0705.4683





– Selection rule for transition between conduction bands

– Valley optoelectronics in metallic system

Dichroic Sum Rules for Ferromagnets

- Interband optical transition, magnetic moment & Berry curvature

$$\eta(\boldsymbol{k}) = -\frac{\boldsymbol{m}(\boldsymbol{k})\cdot\hat{z}}{\mu_B^*(\boldsymbol{k})} = -\frac{\boldsymbol{\Omega}(\boldsymbol{k})\cdot\hat{z}}{\mu_B^*(\boldsymbol{k})}(\varepsilon_c(\boldsymbol{k}) - \varepsilon_i(\boldsymbol{k}))\frac{e}{2\hbar}$$

- Dichroism and orbital magnetization

$$\frac{\mu_B}{2}(\langle f_-\rangle - \langle f_+\rangle) = \hat{z}\cdot\int_{BZ}\frac{d\boldsymbol{k}}{(2\pi)^d}g(\boldsymbol{k})\boldsymbol{m}(\boldsymbol{k}),$$

Total oscillator strength: $\langle f_\pm\rangle \equiv \sum_i \int_{BZ}\frac{d\boldsymbol{k}}{(2\pi)^d}g(\boldsymbol{k})\frac{\left|\mathcal{P}_x^{ci}(\boldsymbol{k}) \pm \mathcal{P}_y^{ci}(\boldsymbol{k})\right|^2}{m_e\left(\varepsilon_c(\boldsymbol{k}) - \varepsilon_i(\boldsymbol{k})\right)}.$

- Dichroism and anomalous Hall conductivity

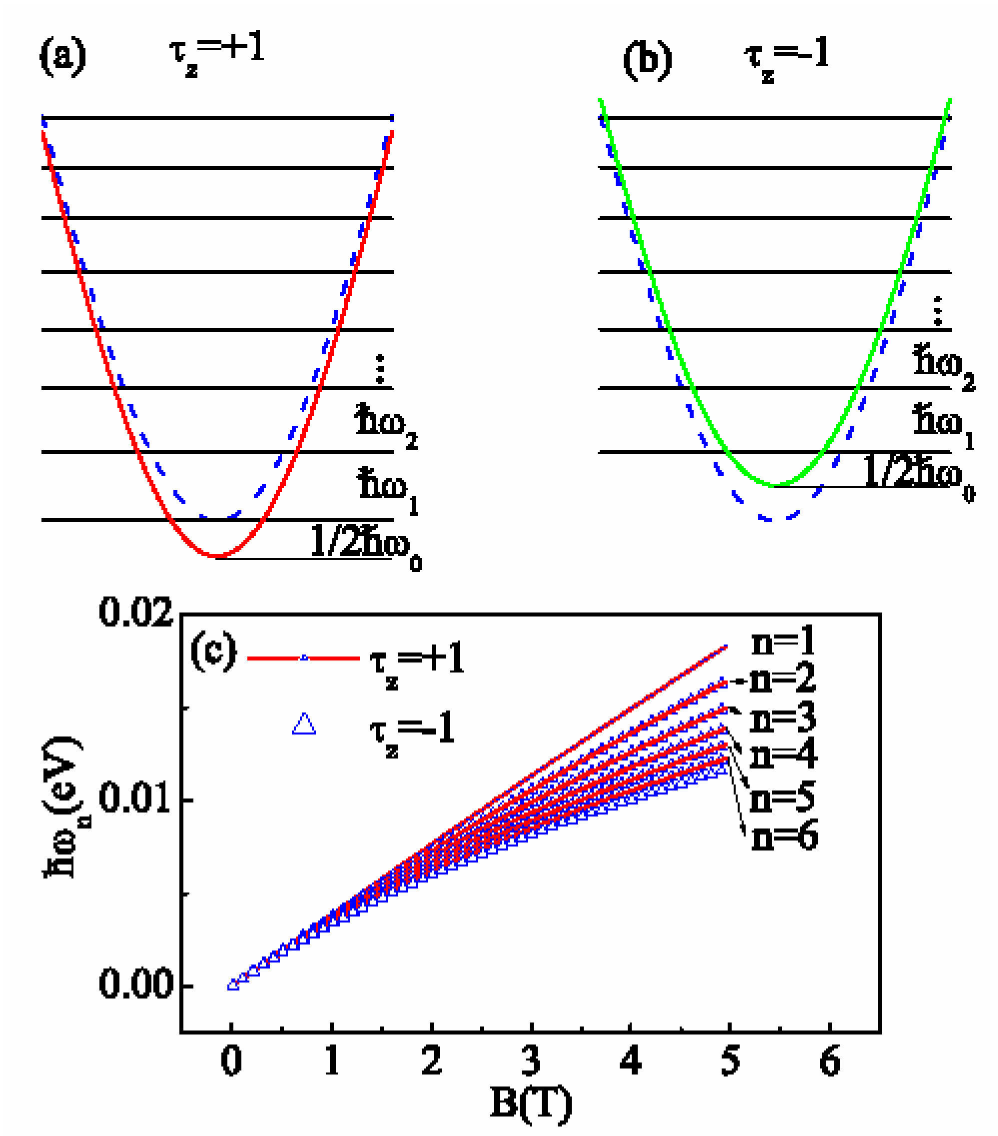
$$\sigma_H = \frac{\epsilon_0}{\pi}\int d\omega(\epsilon_-^i(\omega) - \epsilon_+^i(\omega))$$

Interband absorptions: $\epsilon_\pm^i(\omega) = \frac{\pi e^2}{\epsilon_0 m_e^2\omega^2}\sum_i\int_{BZ}\frac{d\boldsymbol{k}}{(2\pi)^2}g(\boldsymbol{k})\left|\mathcal{P}_x^{ci}(\boldsymbol{k}) \pm i\mathcal{P}_y^{ci}(\boldsymbol{k})\right|^2\delta(\varepsilon_c(\boldsymbol{k}) - \varepsilon_i(\boldsymbol{k}) - \hbar\omega)$

Summary

- Electrons classified by valley index in graphene
- Valley contrasting topological properties from inversion symmetry breaking
- Valley analog of spin electronics and spin optoelectronics
- Generalization to other non-central valley semiconductors, Si or AlAs

Quantum calculations of Landau Levels



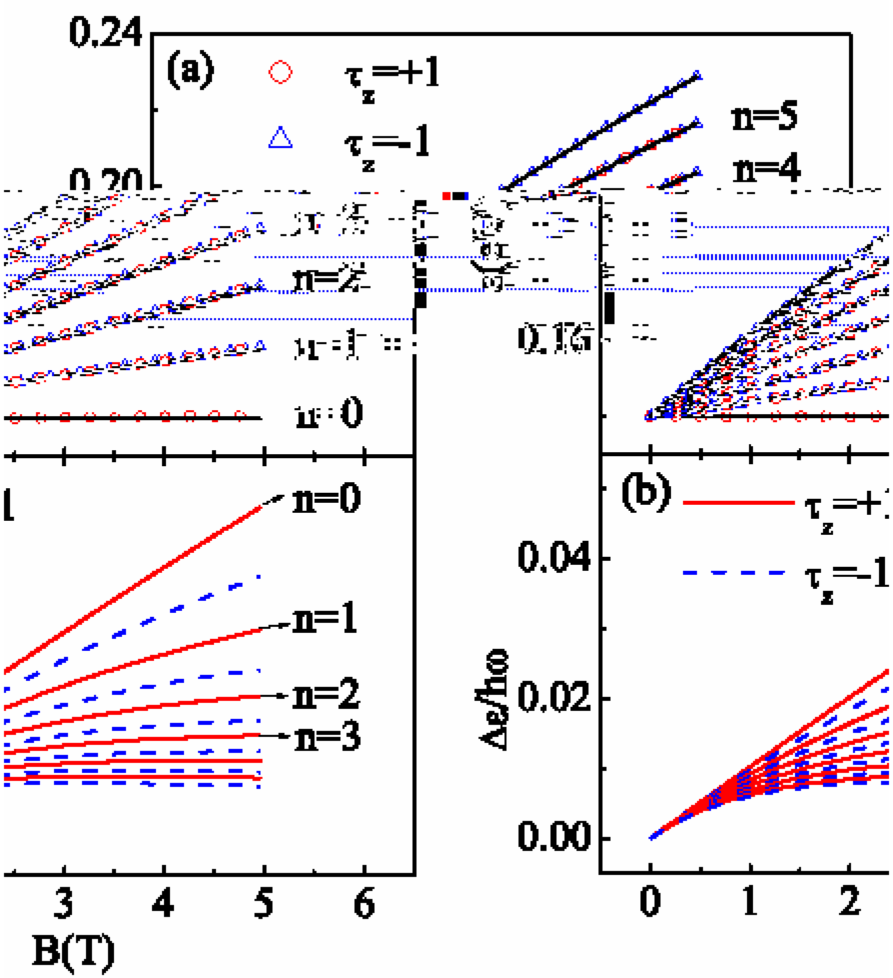
$$E_n = \pm\sqrt{\left(\frac{\Delta}{2}\right)^2 + \frac{3a^2t^2eB}{4Z}\left(2n+1-\tau_z\right)}$$

- The lowest LLs are located at $\frac{1}{2}Z\omega^*$

$$\omega^* = \frac{2Z\Delta}{3a^2t^2}$$

- E_{n+1}-E_n is not a constant, which is related to the Berry curvature.

The comparison in Landau levels



- The field dependence of LLs, E_{semi} (red circle and blue triangle) is obtained from the semiclassical quantum condition.

$$A = \frac{2\pi eB}{Z}\left(n + \frac{1}{2} - \frac{\Gamma}{2\pi}\right)$$

- For comparison, the quantum results are also shown (solid line).